



PTO/SB/08 Equivalent

| | | |
|---|----------------------|--|
| INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Multiple sheets used when necessary) | Application No. | 10/661,414 |
| | Filing Date | September 12, 2003 |
| | First Named Inventor | Gonzalez |
| | Art Unit | 2826 |
| SHEET 1 OF 1 | | Examiner Fetsum Abraham |
| | | Attorney Docket No. MICRON.079DV1C1 |

U.S. PATENT DOCUMENTS

| Examiner Initials | Cite No. | Document Number Number - Kind Code (if known) Example: 1,234,567 B1 | Publication Date MM-DD-YYYY | Name of Patentee or Applicant | Pages, Columns, Lines Where Relevant Passages or Relevant Figures Appear |
|----------------------|-------------|---|--------------------------------|-------------------------------|--|
| FA | | 5,101,251 | 03-31-1992 | Wakamiya, et al. | |
| FA | | 5,395,786 | 03-07-1995 | Hsu, et al. | |
| FA | | 5,658,811 | 08-19-1997 | Kimura, et al. | |
| FA | | 5,668,035 | 09-16-1997 | Fang, et al. | |
| FA | | 5,731,238 | 03-24-1998 | Cavins, et al. | |
| FA | | 5,843,817 | 12-01-1998 | Lee, et al. | |
| FA | | 5,960,289 | 09-28-1999 | Tsui, et al. | |
| FA | | 6,136,728 | 10-24-2000 | Wang | |

FOREIGN PATENT DOCUMENTS

| Examiner Initials | Cite No. | Foreign Patent Document Country Code-Number-Kind Code Example: JP 1234567 A1 | Publication Date MM-DD-YYYY | Name of Patentee or Applicant | Pages, Columns, Lines Where Relevant Passages or Relevant Figures Appear | T ¹ |
|----------------------|-------------|--|-----------------------------------|----------------------------------|--|----------------|
| | | | | | | |
| | | | | | | |

NON PATENT LITERATURE DOCUMENTS

| Examiner Initials | Cite No. | Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published. | T ¹ |
|----------------------|-------------|---|----------------|
| FA | | Sekine et al., "Self-aligned tungsten strapped source/drain and gate technology realizing the lowest sheet resistance for sub-quarter micron CMOS," International Electron Devices Meeting, December 1994, IEEE, p. 493-496 | |
| | | | |
| | | | |
| | | | |

1348736_1
031705

| | |
|---|-------------------------------|
| Examiner Signature <i>Fetsum Abraham</i> | Date Considered <i>5/2/05</i> |
| *Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. | |

T¹ - Place a check mark in this area when an English language Translation is attached.